2SD1026

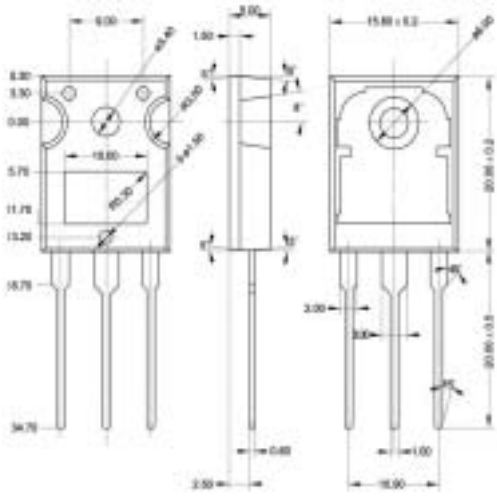
Silicon NPN Transistors

◆ Features

. With TO-247 package

. Darlington transistor

B C E



TO-247

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	100	V
V_{CEO}	Collector to emitter voltage	100	V
V_{EBO}	Emitter to base voltage	7	V
I_B	Base current	1	A
I_C	Collector current	15	A
P_C	Collector power dissipation	100	W
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-55~150	℃

Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{CEO}	Collector breakdown voltage	V_{CE}=100V; I_B=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			5	mA
V_{CBO}	Collector-base breakdown voltage					
V_{CEO}	Collector-emitter breakdown voltage	I_C=30mA; I_B=0	100			V
V_{EBO}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	I_C=10A; I_B=20mA			1.5	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	I_C=10A; V_{CE}=3V	1500		30000	
h_{FE-2}	Forward current transfer ratio					
$V_{BE(sat-1)}$	Base-emitter saturation voltages	I_C=10A; I_B=20mA			2.0	V
$V_{BE(sat-2)}$	Base-emitter saturation voltages					
f_T	Transition frepuency at f=1MHz	I_C=1.5A; V_{CE}=10V		20		MHz